



Pro Electron Bipolar Devices

Device No.	Case Style	V _{CES} * V _{CEO} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CB0} V _{CB} (nA) @ (V) Max	h _{FE} h _{FE} Min Max	I _C & V _{CE} (mA) (V) 1 1	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(ON)} * (V) Min Max	I _C (mA) Min Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Min Max	NF (dB) Max	Test Conditions	Process No.
BC327	TO-92 (97)	50*	45	5	100* 45	40 100 600 1	300 1	0.7	1.2* 500	500						67
BC327A	TO-92 (97)	60*	60	5	100* 45	40 100 400 1	300 1	0.7	1.2* 300	300						67
BC327-16	TO-92 (97)	50*	45	5	100* 45	40 100 250 1	300 1	0.7	1.2* 500	500						67
BC327-25	TO-92 (97)	50*	45	5	100* 45	40 160 400 1	300 1	0.7	1.2* 300	500						67
BC328	TO-92 (97)	30*	25	5	100* 25	40 100 600 1	100 1	0.7	1.2 300	500						67
BC328-25	TO-92 (97)	30*	25	5	100* 25	40 160 400 1	100 1	0.7	1.2 300	500						67
BC337	TO-92 (97)	50*	45	5	100 20	40 100 600 1	100 1	0.7	1.2 500	500						12
BC337A	TO-92 (97)	60*	60	5	100 20	40 100 400 1	100 1	0.7	1.2 500	500						12
BC337-16	TO-92 (97)	50*	45	5	100 20	40 100 250 1	100 1	0.7	1.2 500	500						12
BC337-25	TO-92 (97)	50*	45	5	100 20	40 160 400 1	100 1	0.7	1.2 500	500						12
BC338	TO-92 (97)	30*	20	5	100 20	40 100 600 1	100 1	0.7	1.2 500	500						12
BC368	TO-92 (94)	25*	20	5	10K 25	50 85 375 60	5 10 500 1A	0.5	1A	1A		40	10			37 (6-1)

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device datasheet.